



- High frequency operation
 - Low forward voltage drop
 - High purity, high temperature epoxy encapsulation for enhanced mechanical strength
- Φ M J marked

■ (Ta=25℃ Unless otherwise specified)

Device marking code			GFMK4045
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	IO	A	40
Surge(Non-repetitive)Forward Current @60Hz sine wave, 1 cycle, Tj=25℃	IFSM	A	400
Current Squared Time @1ms≤t<8.3ms Tj=25℃, Rating of per diode	I²t	A²S	660
Storage Temperature	Tstg	-	-55 ~+150
Junction Temperature IN DC Forward Mode-Forward Operations without reverse bias, t≤1 h (Fig. 1)	Tj	-	-55 ~+200

(1) Ta=100℃ 12

IRRM3	mA	VRM=VRRM Ta=125℃	55

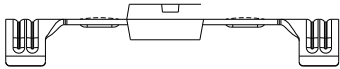
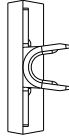
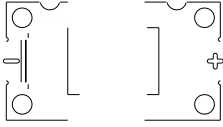


■ (T_a=25℃ Unless otherwise specified)

Thermal Resistance 1	R _{θJ-C}	- /W	1.5

*) 0.

v2XWOLQH 'LPHQVERQOLPHWHUV





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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controller